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<u>Diodes Incorporated</u> 74LVCE1G126W5-7

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## 74LVCE1G126

### SINGLE BUFFER GATE WITH 3-STATE OUTPUT

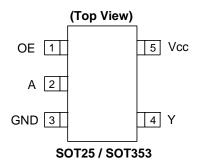
### **Description**

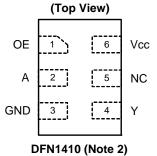
The 74LVCE1G126 is a single non-inverting buffer/bus driver with a 3-state output. The output enters a high impedance state when a LOW-level is applied to the output enable (OE) pin. The device is designed for operation with a power supply range of 1.4V to 5.5V. The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using  $I_{\rm OFF}$ . The  $I_{\rm OFF}$  circuitry disables the output preventing damaging current backflow when the device is powered down.

#### **Features**

- Extended Supply Voltage Range from 1.4 to 5.5V
- Switching speed characterized for operation at 1.5V
- Offers 30% speed improvement over LVC at 1.8V.
- ± 24mA Output Drive at 3.3V
- CMOS low power consumption
- IOFF Supports Partial-Power-Down Mode Operation
- Inputs accept up to 5.5V
- ESD Protection Tested per JESD 22
   Exceeds 200-V Machine Model (A115-A)
   Exceeds 2000-V Human Body Model (A114-A)
- · Latch-Up Exceeds 100mA per JESD 78, Class II
- · Range of Package Options
- · Direct Interface with TTL Levels
- SOT25, SOT353 and DFN1410: Assembled with "Green" Molding Compound (no Br, Sb)
- Lead Free Finish/ RoHS Compliant (Note 1)

### **Pin Assignments**





### **Applications**

- · Voltage Level Shifting
- Bus Driver / Repeater
- Power Down Signal Isolation
- General Purpose Logic
- Wide array of products such as.
  - o PCs, networking, notebooks, netbooks, PDAs
  - Computer peripherals, hard drives, CD/DVD ROM
  - TV, DVD, DVR, set top box
  - o Cell Phones, Personal Navigation / GPS
  - o MP3 players ,Cameras, Video Recorders

Notes: 1. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied. Please visit our website at http://www.diodes.com/products/lead\_free.html.

2. Pin 2 and pin 5 of the DFN1410 package are internally connected.



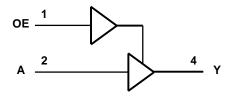


## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

## **Pin Descriptions**

Pin Name	Description				
OE	OE Output Enable (active high)				
Α	Data Input				
GND	Ground				
Υ	Data Output				
Vcc	Supply Voltage				

## **Logic Diagram**



## **Function Table**

Inp	Output			
OE	OE A			
Н	Н	Н		
Н	L	L		
L	Х	Z		





## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

## **Absolute Maximum Ratings (Note 3)**

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD MM	Machine Model ESD Protection	200	V
V <sub>CC</sub>	Supply Voltage Range	-0.5 to 6.5	V
V <sub>I</sub>	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage applied to output in high impedance or I <sub>OFF</sub> state	-0.5 to 6.5	V
Vo	Voltage applied to output in high or low state	-0.3 to V <sub>CC</sub> +0.5	V
I <sub>IK</sub>	Input Clamp Current V <sub>I</sub> <0	-50	mA
I <sub>ok</sub>	Output Clamp Current	-50	mA
Io	Continuous output current	±50	mA
	Continuous current through Vdd or GND	±100	mA
TJ	Operating Junction Temperature	-40 to 150	°C
T <sub>STG</sub>	Storage Temperature	-65 to 150	°C

Note: 3. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.





## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

## **Recommended Operating Conditions (Note 4)**

Symbol		Parameter	Min	Max	Unit	
\/	Operating Voltage	Operating	1.4	5.5	V	
$V_{CC}$	Operating Voltage	Data retention only	1.2		V	
		V <sub>CC</sub> = 1.4 V to 1.95 V	0.65 X V <sub>CC</sub>			
$V_{IH}$	High Lovelles of Maltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V	
V IH	High Level Input Voltage	V <sub>CC</sub> = 3 V to 3.6 V	2		V	
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0.7 X V <sub>CC</sub>			
		$V_{CC} = 1.4 \text{ V to } 1.95 \text{ V}$		0.35 X V <sub>CC</sub>		
\/	Low Level Input Voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V	
$V_{IL}$	Low Level Input Voltage	V <sub>CC</sub> = 3 V to 3.6 V		0.8	V	
		V <sub>CC</sub> = 4.5 V to 5.5 V		0.3 X V <sub>CC</sub>		
Vı	Input Voltage		0	5.5	V	
Vo	Output Voltage		0	V <sub>CC</sub>	V	
	High Level Output	Vcc=1.4 V		-3		
		V <sub>CC</sub> = 1.65 V		-4	mΛ	
		V <sub>CC</sub> = 2.3 V		-8		
I <sub>OH</sub>	Current	V 2V		-16	mA	
		$V_{CC} = 3 V$		-24		
		V <sub>CC</sub> = 4.5 V		-32		
		Vcc=1.4 V		3		
		V <sub>CC</sub> = 1.65 V		4		
	Low Level Output	V <sub>CC</sub> = 2.3 V		8	mA	
$I_{OL}$	Current	V 2V		16		
		$V_{CC} = 3 V$		24		
		V <sub>CC</sub> = 4.5 V		32		
		V <sub>CC</sub> = 1.4 to 3V		20		
$\Delta t/\Delta V$	Input transition rise or fall	V <sub>CC</sub> = 3.3 V ± 0.3 V		10	ns/V	
	rate	$V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$		5		
T <sub>A</sub>	Operating free-air temperature		-40	85	°C	

Note: 4. Unused inputs should be held at Vcc or Ground.





## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

### Electrical Characteristics (All typical values are at Vcc = 3.3V, T<sub>A</sub> = 25°C)

Over recommended free-air temperature range (unless otherwise noted)

Symbol	Parameter	<b>Test Conditions</b>	Vcc	Min	Тур.	Max	Unit	
		I <sub>OH</sub> = -100μA	1.4 V to 5.5V	V <sub>CC</sub> - 0.1				
		$I_{OH} = -3mA$	1.4 V	1.05			1	
	High Laval Output	$I_{OH} = -4mA$	1.65 V	1.2			]	
$V_{OH}$	High Level Output Voltage	$I_{OH} = -8mA$	2.3V	1.9			V	
	Voltage	I <sub>OH</sub> = -16mA	3 V	2.4			]	
		$I_{OH} = -24mA$	3 V	2.3				
		$I_{OH} = -32mA$	4.5 V	3.8			]	
		$I_{OL} = 100 \mu A$	1.4 V to 5.5V			0.1		
		$I_{OL} = 3mA$	1.4V			.4	]	
		$I_{OL} = 4mA$	1.65 V			0.45	1	
$V_{OL}$	Low Level Output Voltage	$I_{OL} = 8mA$	2.3V			0.3	V	
	Voltage	$I_{OL} = 16mA$	3 V			0.4		
		$I_{OL} = 24mA$	3 V			0.55		
		$I_{OL} = 32mA$	4.5			0.55	1	
I <sub>I</sub>	Input Current	$V_1 = 5.5 \text{ V or GND}$	0 to 5.5 V			± 5	μΑ	
I <sub>OFF</sub>	Power Down Leakage Current	$V_1$ or $V_0 = 5.5V$	0			± 10	μΑ	
I <sub>OZ</sub>	Z State Leakage Current	V <sub>O</sub> =0 to 5.5V	3.6V			10	μΑ	
I <sub>cc</sub>	Supply Current	$V_1 = 5.5V$ of GND $I_0=0$	1.4 V to 5.5V			10	μΑ	
$\Delta I_{CC}$	Additional Supply Current	One input at V <sub>CC</sub> – 0.6 V Other inputs at V <sub>CC</sub> or GND	3 V to 5.5V			500	μA	
Ci	Input Capacitance	$V_i = V_{CC} - \text{ or GND}$	3.3		3.5		pF	
		SOT25	(Note 5)		204			
$\theta_{JA}$	Thermal Resistance Junction-to-Ambient	SOT353	(Note 5)		371		°C/W	
	Junction-to-Ambient	DFN1410	(Note 5)		430		1	
		SOT25	(Note 5)		52			
$\theta_{JC}$	Thermal Resistance	SOT353	(Note 5)		143		°C/W	
	Junction-to-Case	DFN1410	(Note 5)		190			

Note: 5. Test condition for SOT25, SOT353 and DFN1410: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.





## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

## **Switching Characteristics**

Over recommended free-air temperature range, CL = 15pF (see Figure 1)

Parameter	± 0.1 V		Vcc = 1.8 V Vcc = 2.5 V ± 0.15V ± 0.2V			5 V Vcc = 3.3 V + 0.3 V		Vcc = 5 V ± 0.5V		Unit			
	(Input)	(OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
$t_{pd}$	A	Y	1.7	6.9	1.1	4.8	0.4	3.6	0.4	3	0.4	3	ns

Over recommended free-air temperature range, CL = 30 or 50pF as noted (see Figure 2)

Parameter	From TO		± U. I V				Vcc = 2.5 V ± 0.2V		Vcc = 3.3 V ± 0.3V		Vcc = 5 V ± 0.5V		Unit
	(Input)	(OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
t <sub>pd</sub>	А	Υ	2.6	8	1.8	5.6	0.8	4.4	0.8	3.6	0.9	3.6	ns
t <sub>en</sub>	ŌE	Y	2.8	9.4	1.9	6.5	1	5.2	0.9	4.3	0.9	4.3	
t <sub>dis</sub>	ŌĒ	Y	1.6	9.8	1.1	6.8	0.8	4.4	0.8	4.5	0.9	3.7	

### **Operating Characteristics**

 $T_A = 25$  °C

	Parameter		Test	Vcc = 1.5 V	Vcc = 1.8 V	Vcc = 2.5 V	Vcc = 3.3 V	Vcc = 5 V	Unit
			Conditions	TYP	TYP	TYP	TYP	TYP	
	Power	Outputs enabled	f = 10 MHz	19	19	19	19	19	~F
C <sub>pd</sub>	dissipation capacitance	Outputs disabled	I = IU WIMZ	2	2	2	3	4	pF

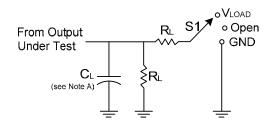




## 74LVCE1G126

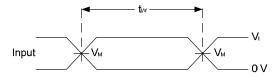
### SINGLE BUFFER GATE WITH 3-STATE OUTPUT

#### **Parameter Measurement Information**

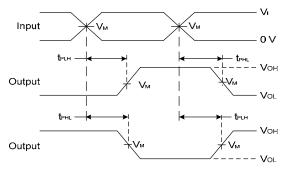


TEST	S1
t <sub>PLH</sub> /t <sub>PHL</sub>	Open
t <sub>PLZ</sub> /t <sub>PZL</sub>	Vload
t <sub>PHZ</sub> /t <sub>PZH</sub>	GND

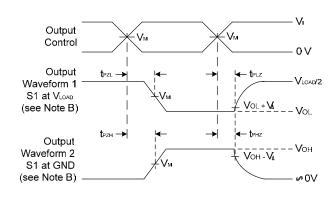
Vcc	Inj	puts	V		
VCC	Vı	t <sub>r</sub> /t <sub>f</sub>	- V <sub>M</sub>	CL	RL
1.5V±0.1V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	15pF	1ΜΩ
1.8V±0.15V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	15pF	1ΜΩ
2.5V±0.2V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	15pF	1ΜΩ
3.3V±0.3V	3V	≤2.5ns	1.5V	15pF	1ΜΩ
5V±0.5V	V <sub>cc</sub>	≤2.5ns	V <sub>CC</sub> /2	15pF	1ΜΩ



### **Voltage Waveform Pulse Duration**



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs



Voltage Waveform Enable and Disable Times Low and High Level Enabling

Notes: A. Includes test lead and test apparatus capacitance.

B. All pulses are supplied at pulse repetition rate ≤ 10 MHz.

C. Inputs are measured separately one transition per measurement.

D.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis.}$ 

E.  $t_{\text{PZL}}$  and  $t_{\text{PZH}}$  are the same as  $t_{\text{EN}}$ .

F.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{PD.}$ 

Figure 1. Load Circuit and Voltage Waveforms

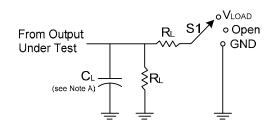




## 74LVCE1G126

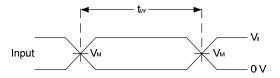
### SINGLE BUFFER GATE WITH 3-STATE OUTPUT

#### **Parameter Measurement Information (Continued)**

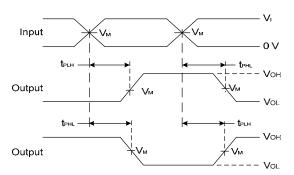


TEST	S1
t <sub>PLH</sub> /t <sub>PHL</sub>	Open
$t_{PLZ}/t_{PZL}$	Vload
t <sub>PHZ</sub> /t <sub>PZH</sub>	GND

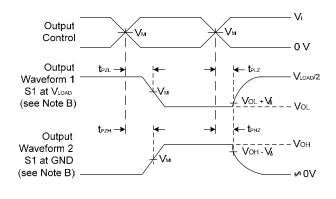
Vcc	Inp	outs	V <sub>M</sub>	CL	RL
	Vı	t <sub>r</sub> /t <sub>f</sub>	- IVI	J.	
1.5V±0.1V	V <sub>cc</sub>	≤2ns	V <sub>CC</sub> /2	30pF	1ΚΩ
1.8V±0.15V	V <sub>cc</sub>	≤2ns	V <sub>CC</sub> /2	30pF	1ΚΩ
2.5V±0.2V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	30pF	500Ω
3.3V±0.3V	3V	≤2.5ns	1.5V	50pF	500Ω
5V±0.5V	V <sub>cc</sub>	≤2.5ns	V <sub>CC</sub> /2	50pF	500Ω



#### **Voltage Waveform Pulse Duration**



Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs



Voltage Waveform Enable and Disable Times Low and High Level Enabling

- Notes: A. Includes test lead and test apparatus capacitance.
  - B. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
  - C. Inputs are measured separately one transition per measurement.
  - D.  $t_{\text{PLZ}}$  and  $t_{\text{PHZ}}$  are the same as  $t_{\text{dis.}}$
  - E.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{EN0}$
  - F.  $t_{\text{PLH}}$  and  $t_{\text{PHL}}$  are the same as  $t_{\text{PD.}}$

Figure 2. Load Circuit and Voltage Waveforms





## 74LVCE1G126

## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

## **Ordering Information**

T4LVCE1G 126 XXX - 7

Logic Device Function Package Packing

74: Logic Prefix 126: 3-State Buffer W5: SOT25 7: Tape & Reel

LVCE : 1.4 to 5.5V OE-High SE : SOT353 FZ4 : DFN1410

1G: One gate

	Device	Package	Packaging	7" Tape and Reel	
	Device	Code	(Note 5)	Quantity	Part Number Suffix
<b>Pb</b> ,	74LVCE1G126W5-7	W6	SOT25	3000/Tape & Reel	-7
<b>Pb</b> ,	74LVCE1G126SE-7	SE	SOT353	3000/Tape & Reel	-7
<b>Pb</b> ,	74LVCE1G126FZ4-7	FZ4	DFN1410	5000/Tape & Reel	-7

Note: 6. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.







## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

### **Marking Information**

### (1) SOT25 and SOT353

### (Top View)

5 4 XX Y WX

2

1

XX: Identification code

Y: Year 0~9

<u>W</u>: Week: A~Z: 1~26 week;

a~z: 27~52 week; z represents

52 and 53 week X: A~Z: Internal code

Part Number	Package	Identification Code	
74LVCE1G126W5	SOT25	PZ	
74LVCE1G126SE	SOT353	PZ	

### (2) DFN1410

### (Top View)

3

XX XX: Identification Code

Y: Year: 0~9

<u>W</u>: Week: A~Z: 1~26 week; a~z: 27~52 week; z represents

52 and 53 week X: A~Z: Internal code

**Part Number Package Identification Code** 74LVCE1G126FZ4 DFN1410 PΖ



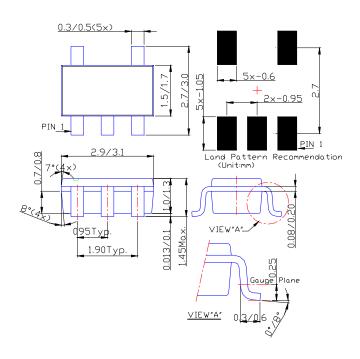


## 74LVCE1G126

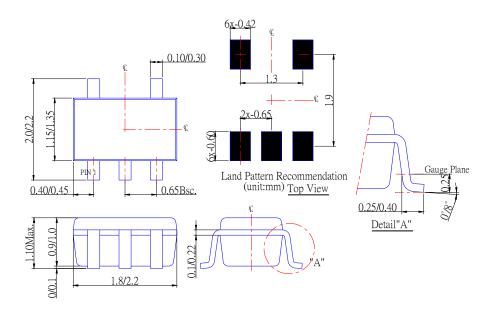
## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

## Package Outline Dimensions (All Dimensions in mm)

### (1) Package Type: SOT25



### (2) Package Type: SOT353





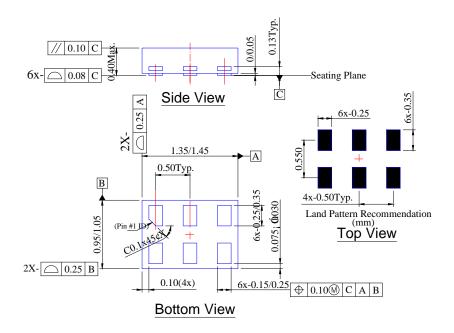


## 74LVCE1G126

## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

## Package Outline Dimensions (All Dimensions in mm)

### (3) Package Type: DFN1410



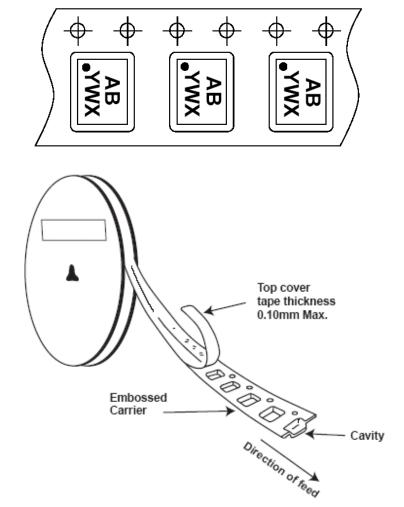




## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

## **Taping Orientation (Note 7)**

#### For DFN1410



Note: 7. The taping orientation of the other package type can be found on our website at http://www.diodes.com/datasheets/ap02007.pdf



### SINGLE BUFFER GATE WITH 3-STATE OUTPUT

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